NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI ASAT10** is Designed for

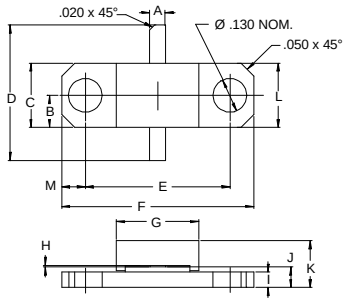
FEATURES:

- Input Matching Network
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- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	2.3 A
V_{CBO}	45 V
V_{CEO}	15 V
V_{EBO}	3.5 V
P_{DISS}	29 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +150 ^{O}C
θ_{JC}	6.0 ^{O}C/W

PACKAGE STYLE .250 2L FLG(A)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.055 / 1.40	.065 / 1.65
B	.124 / 3.15	
C	.243 / 6.17	.253 / 6.43
D	.635 / 16.13	.665 / 16.89
E	.555 / 14.10	.565 / 14.35
F	.739 / 18.77	.749 / 19.02
G	.315 / 8.00	.325 / 8.26
H	.002 / 0.05	.006 / 0.15
I	.055 / 1.40	.065 / 1.65
J	.075 / 1.91	.095 / 2.41
K		.190 / 4.83
L	.245 / 6.22	.255 / 6.48
M	.092 / 2.34	

ORDER CODE: ASI10517

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 3.0 mA	45			V
BV_{CEO}	I_C = 3.0 mA	12			V
BV_{EBO}	I_E = 3.0 mA	3.5			V
h_{FE}	V_{CE} = 5.0 V I_C = 600 mA	15		150	---
C_{OB}	V_{CB} = 28 V f = 1.0 MHz			7.0	pF
P_G	V_{CC} = 28 V P_{OUT} = 10 W f = 1.65 GHz	11			dB
η_C		45			%

Specifications are subject to change without notice.